

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-6 (canceled)

7. (Currently amended) A protection film for a thin film device formed on a substrate, which comprises a hydrogen content of not less than 30 at%, wherein the protection film is one of SiN, SiO, SiON, SiC or SiCN, and the protection film has a thickness of 1-5 μ m.

8. (canceled)

9. (Currently amended) An organic electroluminescent device which comprises at least a first electrode, an organic luminescent layer, and a second electrode formed on a substrate, wherein the organic electroluminescent device further comprises a protection film which covers the organic electroluminescent device and of which hydrogen content is not less than 30at%, wherein the protection film is one of SiN, SiO, SiON, SiC or SiCN, and the protection film has a thickness of 1-5 μ m.

10. (canceled)

11. (Currently amended) A process for manufacturing an organic electroluminescent device which comprises at least a first electrode, an organic luminescent layer, and an second electrode formed on a substrate, which comprises forming a protection film which covers the organic electroluminescent device, wherein hydrogen content of the protection film is not less than 30at% through the use of CVD method or ~~spatterings~~sputtering method, wherein the protection film is one of SiN, SiO, SiON, SiC or SiCN, and the protection film has a thickness of 1-5 μm .

12. (Previously presented) A process according to Claim 11, wherein the CVD method is plasma CVD method.